



# 2-Output Low Power PCIE Gen 1-2-3 Clock Generator

#### **Features**

- → 25MHz crystal or reference clock input
- → 100MHz low power HCSL or LVDS compatible outputs
- → PCIe 3.0, 2.0 and 1.0 compliant
- $\rightarrow$  Selectable spread spectrum of -0.25%, -0.5% and no spread
- → Programmable output amplitude and slew rate
- → Cycle-to-cycle jitter (typ.) ~ 30ps
- → Supply voltage of 3.3V+/-10%
- → Output supply voltage of 1.8V (1.05V to 3.6V supported)
- → Industrial ambient operating temperature
- → Available in lead-free package: 24-TQFN

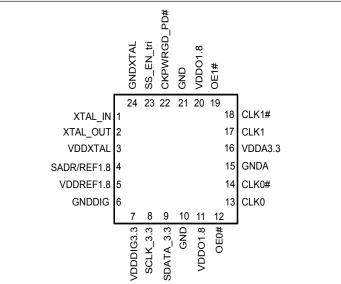
#### Description

The PI6CFGL201B is a 2-output very low power 100MHz frequency generator for PCIe Gen 1, 2 and 3 applications with integrated output terminations providing  $Zo=100\Omega$ . The device has 2 output enables for clock management and supports 2 different spread spectrum levels in additon to spread off. The device also has one 1.8V LVCMOS REF1.8 output.

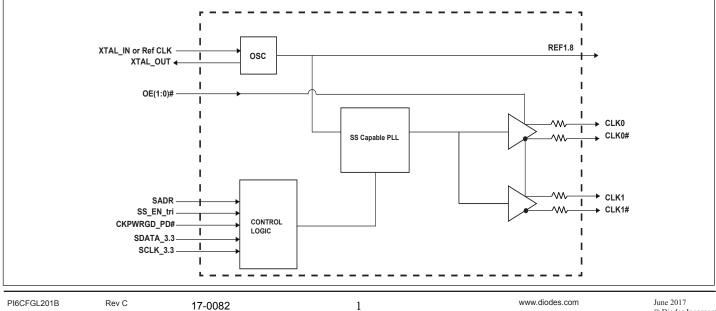
## **Applications**

→ PCIe 3.0/2.0/1.0 clock generation

# Pin Configuration (24-Pin TQFN)



#### **Block Diagram**

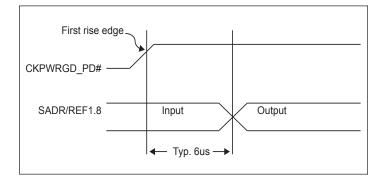






# **SMBus Address Selection Table**

	SADR	Address	+ Read/Write Bit
State of SADR on first application of CKPWRGD_PD#	0	1101000	1/0
	1	1101010	1/0



## **Power Management Table**

CVDWDCD DD#	SMBus OE bit	CI	REF1.8		
CKPWRGD_PD#	SMIDUS OE DI	True O/P	Comp. O/P	KEF1.8	
0	Х	Low	Low	Hi-Z <sup>1</sup>	
1	1	Running	Running	Running	
1	0	Low	Low	Low	

#### Note:

1. REF1.8 is Hi-Z until the 1st assertion of CKPWRGD\_PD# high. After this, when CKPWRG\_PD# is low, REF1.8 is Low.

CKDWRCD DD#	OE(D;r)	OF (SMD-rehit)	CI	.Kx
CKPWRGD_PD#	OE (Pin)	OE (SMBus bit)	True O/P	Comp. O/P
0	X	X	Low	Low
1	0	0	Low	Low
1	0	1	Running	Running
1	1	0	Low	Low
1	1	1	Low	Low

#### **Typical Crystal Requirement**

Parameter	Test Conditions	Min.	Туре	Max.	Units
Mode of Oscillation		Fundamental			
Frequency			25		MHz
Equivalent Series Resistance (ESR)					Ω
Shunt Capacitance					pF

# **Recommended Crystal Specification**

a) FL2500047, SMD 3.2X2.5(4P), 25MHz, CL=18pF, +/-20ppm, http://www.pericom.com/pdf/datasheets/se/FL.pdf

b) FY2500091, SMD 5x3.2(4P), 25MHz, CL=18pF, +/-30ppm, http://www.pericom.com/pdf/datasheets/se/FY F9.pdf





## **Pin Description**

Pin#	Pin Name	Туре	Description
1	XTAL_IN	Input	Crystal input or reference input clock, Nominally 25.00MHz.
2	XTAL_OUT	Output	Crystal output.
3	VDDXTAL	Power	3.3V Power supply for XTAL.
4	SADR/REF1.8	Input/Output	Latch to select SMBus Address/1.8V LVCMOS REF1.8 output. This pin has an internal pull-down.
5	VDDREF1.8	Power	Power supply for the REF1.8 output
6	GNDDIG	Power	Ground pin for digital circuitry
7	VDDDIG3.3	Power	3.3V digital power (dirty power)
8	SCLK_3.3	Input	Clock pin of SMBus circuitry, 3.3V tolerant.
9	SDATA_3.3	Input/Output	Data pin for SMBus circuitry, 3.3V tolerant.
10	GND	Power	Ground pin.
11	VDDO1.8	Power	Power supply, nominal 1.8V, range 1.05V~3.6V.
12	OE0#	Input	Active low input for enabling CLK0 pair 0. This pin has an internal pull-down. 1 =disable outputs, 0 = enable outputs
13	CLK0	Output	Differential true clock output
14	CLK0#	Output	Differential Complementary clock output
15	GNDA	Power	Ground pin for the PLL core.
16	VDDA3.3	Power	3.3V power for the PLL core.
17	CLK1	Output	Differential true clock output
18	CLK1#	Output	Differential Complementary clock output
19	OE1#	Input	Active low input for enabling CLK1 pair 1. This pin has an internal pull-down. 1 =disable outputs, 0 = enable outputs
20	VDDO1.8	Power	Power supply, nominal 1.8V, range 1.05V~3.6V.
21	GND	Power	Ground pin.
22	CKPWRGD_ PD#	Input	Input notifies device to sample latched inputs and start up on first high assertion. Low enters Power Down Mode, subsequent high assertions exit Power Down Mode. This pin has internal pull-up resistor.
23	SS_EN_tri	Input	Latched select input to select spread spectrum amount at initial power up : 1 = -0.5% spread, M = -0.25%, 0 = Spread Off This pin has an internal pull-down.
24	GNDXTAL	Power	GND for XTAL
	Exposed Thermal Pad	-	Connect to Ground





#### Maximum Ratings

(Above which useful life may be impaired. For user guidelines, not tested.)

Supply Voltage to Ground Potential (All VDDx except VDDO)4.6V
Supply Voltage to Ground Potential (VDDO)
All Inputs and Output0.5V to $V_{\text{DD}}\text{+}0.5\text{V}$
Storage Temperature65°C to +150°C
ESD Protection (Input)2000V(HBM)

Note: Stresses greater than those listed under MAXIMUM RAT-INGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

# **Electrical Characteristics-Current Consumption**

 $(T_A = -40 \sim 85^{\circ}C; VDD = 3.3V + /-10\%; VDDO = 1.8V + /-10\%$ , See Test Loads for Loading Conditions)

Symbol	Parameters	Condition	Min.	Туре	Max.	Units
I <sub>DDA</sub>		VDDA3.3, PLL Mode, core current consumption		29	38	mA
I <sub>ddop</sub>	Operating Supply Current <sup>1</sup>	VDDO, output only current consumption. All outputs active		6	8	mA
I <sub>ddtotal</sub>		Total current consumption. All outputs active @100MHz		35	46	mA
I <sub>ddsusp</sub>	Suspend Supply Current <sup>1</sup>	VDDxxx, CKPWRGD_PD# = 0, Wake-On-LAN enabled		4.5	8	mA
I <sub>ddpd</sub>	Powerdown Current <sup>1,2</sup>	CKPWRGD_PD#=0		1.3	1.8	mA

#### Notes:

1. Guaranteed by design and characterization, not 100% tested in production.

2. Assuming REF1.8 is not running in power down state.

# Electrical Characteristics-Differential Output Duty Cycle, Jitter, and Skew **Characterisitics**

 $(T_A = -40 \sim 85^{\circ}C; VDD = 3.3V + /-10\%; VDDO = 1.8V + /-10\%$ , See Test Loads for Loading Conditions)

Symbol	Parameters	Condition	Min.	Туре	Max.	Units
t <sub>DC</sub>	Duty Cycle <sup>1</sup>	Measured differentially, PLL Mode	45		55	%
t <sub>sk</sub>	Skew, Output to Output <sup>1</sup>	V <sub>T</sub> = 50%			50	ps
t <sub>jcyc-cyc</sub>	Jitter, Cycle to cycle <sup>1</sup>	PLL mode			50	ps

#### Notes:

1. Guaranteed by design and characterization, not 100% tested in production.





#### **Electrical Characteristics-Input/Supply/Common Parameters**

(Based on  $T_A = -40 \sim 85^{\circ}$ C; VDD = 3.3V +/-10%; VDDO = 1.8V +/-10%, See Test Loads for Loading Conditions)

Symbol	Parameters	Condition	Min.	Туре	Max.	Units
V <sub>DDX</sub>	Supply Voltage <sup>1</sup>	Supply voltage for core, analog	3.0	3.3	3.6	V
V <sub>ddo</sub>	Supply Voltage <sup>1</sup>	Supply voltage outputs	1.05	1.8	3.6	V
T <sub>A</sub>	Ambient Operating Temperature <sup>1</sup>		-40	25	85	°C
V <sub>IH</sub>	Input High Voltage <sup>1</sup>	Single-ended inputs, except SMBus, SS_EN_tri	0.65 V <sub>DD</sub>		V <sub>DD</sub> +0.3	V
V <sub>IM</sub>	Input Mid Voltage <sup>1</sup>	SS_EN_tri	$0.4 \mathrm{V_{DD}}$		0.6 V <sub>DD</sub>	V
V <sub>IL</sub>	Input Low Voltage <sup>1</sup>	Single-ended inputs, except SMBus, SS_EN_tri	-0.3		0.35 V <sub>DD</sub>	V
V <sub>T+</sub>	Schmitt Trigger Postive Going Threshold Voltage <sup>1</sup>	Single-ended inputs, except SS_EN_tri	0.5 V <sub>DD</sub>		0.6 V <sub>DD</sub>	V
V <sub>T-</sub>	Schmitt Trigger Negative Going Threshold Voltage <sup>1</sup>	Single-ended inputs, except SS_EN_tri	$0.4  \mathrm{V}_{\mathrm{DD}}$		$0.5 \mathrm{V}_{\mathrm{DD}}$	V
V <sub>H</sub>	Hysteresis Voltage <sup>1</sup>	V <sub>T+</sub> - V <sub>T-</sub>	0.05 V <sub>DD</sub>		0.2 V <sub>DD</sub>	V
V <sub>oh</sub>	Output High Voltage <sup>1</sup>	Single-ended outputs, except SMBus. I <sub>OH</sub> = -2mA	V <sub>DD</sub> -0.45			V
V <sub>ol</sub>	Outputt Low Voltage <sup>1</sup>	Single-ended outputs, except SMBus. I <sub>OL</sub> = -2mA			0.45	v
I <sub>IN</sub>		Single-ended inputs, $V_{IN} = GND$ , $V_{IN} = VDD$ (exclude XTAL_IN pin)	-5		5	uA
$I_{INP}$	Input Current <sup>1</sup>	Single-ended inputs $V_{IN} = 0$ V; Inputs with internal pull-up resistors $V_{IN} = VDD$ ; Inputs with internal pull-down resistors	-200		200	uA
fin	Input Frequency <sup>1</sup>	XTAL, or XTAL_IN	23	25	26	MHz
Lpin	Pin Inductance <sup>1</sup>				7	nH
C <sub>IN</sub>		Control Inputs	1.5		5	pF
Cout	Capacitance <sup>1</sup>	Output pin capacitance			6	pF
t <sub>stab</sub>	Clock output Stabiliza- tion <sup>1, 2</sup>	From V <sub>DD</sub> Power-Up and after input clock stabilization or de-assertion of CKPWRGD_ PD# to 1st clock		0.6	1	ms
f <sub>modin</sub>	Input SS Modulation Frequency <sup>1</sup>	Allowable Frequency (Triangular Modulation)	30	31.500	33	kHz
t <sub>latoe#</sub>	OE# Latency <sup>1, 3</sup>	CLK start after OE# assertion CLK stop after OE# deassertion	1		3	clocks
t <sub>drvpd</sub>	Tdrive_PD# <sup>1, 3</sup>	CLK output enable after CKPWRGD_PD# de-assertion			300	us





### **Electrical Characteristics-Input/Supply/Common Parameters**

(Based on  $T_A = -40 \sim 85^{\circ}$ C; VDD = 3.3V +/-10%; VDDO = 1.8V +/-10%, See Test Loads for Loading Conditions)

Symbol	Parameters	Condition	Min.	Туре	Max.	Units
t <sub>F</sub>	Fall time <sup>1, 2</sup>	Control inputs			5	ns
t <sub>R</sub>	Rise time <sup>1, 2</sup>	Control inputs			5	ns
V <sub>ILSMB</sub>	SMBus Input Low Voltage <sup>1</sup>				0.8	V
V <sub>IHSMB</sub>	SMBus Input High Voltage <sup>1</sup>		2.1		3.6	V
V <sub>olsmb</sub>	SMBus Output Low Voltage <sup>1</sup>	@ I <sub>pullup</sub>			0.4	V
I <sub>pullup</sub>	SMBus Sink Current <sup>1</sup>	@V <sub>ol</sub>	4			mA
V <sub>ddsmb</sub>	Nominal Bus Voltage <sup>1</sup>	3.3V bus voltage	2.7		3.6	V
t <sub>RSMB</sub>	SCLK/SDATA Rise Time <sup>1</sup>	(Max VIL - 0.15) to (Min VIH + 0.15)			1000	ns
t <sub>FSMB</sub>	SCLK/SDATA Fall Time <sup>1</sup>	(Min VIH + 0.15) to (Max VIL - 0.15)			300	ns
f <sub>maxsmb</sub>	SMBus Operating Frequency <sup>1, 5</sup>	Maximum SMBus operating frequency			400	kHz

Note:

1. Guaranteed by design and characterization, not 100% tested in production.

2. Control input must be monotonic from 20% to 80% of input swing. Input Frequency Capacitance

3. Time from deassertion until outputs are >200 mV

4. The differential input clock must be running for the SMBus to be active

### **Electrical Characteristics-CLK 0.7V Low Power HCSL Outputs**

 $(T_A = -40 \sim 85^{\circ}C; VDD = 3.3V + /-10\%; VDDO = 1.8V + /-10\%$ , See Test Loads for Loading Conditions)

Symbol	Parameters	Condition	Min.	Туре	Max.	Units
tf.	Slew rate <sup>1, 2, 3</sup>	Scope averaging on 1.5V/ns setting	0.9	1.4	1.9	V/ns
trf	Slew rate. <sup>2,3</sup>	Scope averaging on 3.0V/ns setting	1.8	2.9	4	V/ns
Δtrf	Slew rate matching <sup>1, 2, 4</sup>	Slew rate matching, Scope averaging on			20	%
V <sub>oh</sub>	Voltage High <sup>1,7</sup>	Statistical measurement on single-ended signal	660		850	mV
V <sub>OL</sub>	Voltage Low <sup>1,7</sup>	using oscilloscope math function. (Scope averaging on)			150	mV
Vmax	Max Voltage <sup>1</sup>	Measurement on single ended signal using			1150	mV
Vmin	Min Voltage <sup>1</sup>	absolute value. (Scope averaging off)	-300			mV
Vswing	Vswing <sup>1, 2, 7</sup>	Scope averaging off	300			mV
Vcross_abs	Crossing Voltage (abs) <sup>1,</sup> <sup>5,7</sup>	Scope averaging off	250		550	mV
$\Delta$ -Vcross	Crossing Voltage (var) <sup>1, 6</sup>	Scope averaging off			140	mV

Note:

1. Guaranteed by design and characterization, not 100% tested in production.

2. Measured from differential waveform

3. Slew rate is measured through the Vswing voltage range centered around differential 0V. This results in a +/-150mV window around differential 0V.

4. Matching applies to rising edge rate for Clock and falling edge rate for Clock#. It is measured using a +/-75mV window centered on the average cross point where Clock rising meets Clock# falling. The median cross point is used to calculate the voltage thresholds the oscilloscope is to use for the edge rate calculations

5. Vcross is defined as voltage where Clock = Clock # measured on a component test board and only applies to the differential rising edge (i.e. Clock rising and Clock# falling).

6. The total variation of all Vcross measurements in any particular system. Note that this is a subset of Vcross\_min/max (Vcross absolute) allowed. The intent is to limit Vcross induced modulation by setting Δ-Vcross to be smaller than Vcross absolute.

7. At default SMBus settings.

Rev C

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#### **Electrical Characteristics–Phase Jitter Parameters**

 $(T_{A} = -40 \sim 85^{\circ}C; VDD = 3.3V + /-10\%; VDDO = 1.8V + /-10\%$ , See Test Loads for Loading Conditions)

Symbol	Parameters	Condition	Min.	Туре	INDUSTRY LIMIT	Units
t 1, 2, 3, 5 jphPCIeG1	Phase Jitter, PCI Express	PCIe Gen 1		30	86	ps (p-p)
t 1, 2, 5		PCIe Gen 2 Low Band 10kHz < f < 1.5MHz		0.5	3	ps (rms)
t <sub>jphPCIeG2</sub>		PCIe Gen 2 High Band 1.5MHz < f < Nyquist (50MHz)		2.2	3.1	ps (rms)
t, 2, 4, 5 jphPCIeG3		PCIe Gen 3 (PLL BW of 2-4MHz, CDR = 10MHz)		0.46	1	ps (rms)

Notes:

1. Guaranteed by design and characterization, not 100% tested in production.

2. See http://www.pcisig.com for complete specs.

3. Sample size of at least 100k cycles. This figures extrapolates to 108ps pk-pk @ 1M cycles for a BER of 1-12.

4. Calculated from Intel-supplied Clock Jitter Tool.

5. Applies to all different outputs.

### **Electrical Characteristics-REF1.8**

 $(T_A = -40 \sim 85^{\circ}C; VDD = 3.3V + /-10\%; VDDO = 1.8V + /-10\%$ , See Test Loads for Loading Conditions)

Symbol	Parameters	Condition	Min.	Туре	Max.	Units
ppm	Long Accuracy <sup>1, 2</sup>	see Tperiod min-max values		0		ppm
T <sub>period</sub>	Clock period <sup>1, 2</sup>	25 MHz output nominal		40		ns
t <sub>rf1</sub>	Rise/Fall Slew Rate <sup>1, 3</sup>	$V_{OH} = VDD-0.45V, V_{OL} = 0.45V$	0.5		2.5	V/ns
t <sub>DC</sub>	Duty Cycle <sup>1, 4</sup>	$V_{T} = VDDO/2 V$	45		55	%
t <sub>DCD</sub>	Duty Cycle Distortion <sup>1, 5</sup>	$V_{T} = VDDO/2 V$	0		3	%
t <sub>jc-c</sub>	Jitter, cycle to cycle <sup>1, 4</sup>	$V_{T} = VDDO/2 V$			250	ps
t <sub>jdBc1k</sub>	Noise floor <sup>1, 4</sup>	1kHz offset		-141	-120	dBc
t <sub>idBc10k</sub>	Noise floor <sup>1, 4</sup>	10kHz offset to Nyquist		-150	-130	dBc
t <sub>jphREF</sub>	Jitter, phase <sup>1, 4</sup>	12kHz to 5MHz		0.46	1	ps (rms)

#### Notes:

1. Guaranteed by design and characterization, not 100% tested in production.

2. All Long Term Accuracy and Clock Period specifications are guaranteed assuming that REF1.8 is trimmed to 25.00 MHz.

3. Typical value occurs when REF1.8 slew rate is set to default value.

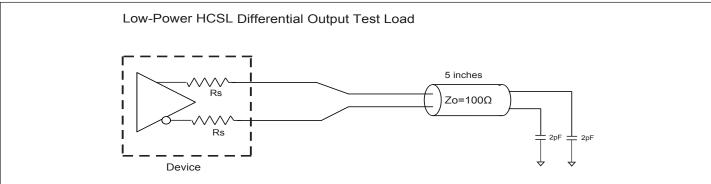
4. When driven by a crystal.

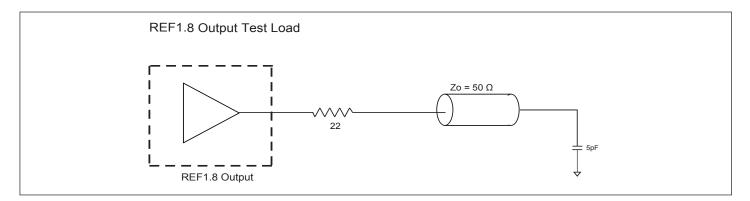
5. When driven by an external oscillator via the XTAL\_IN pin. XTALK\_OUT should be floating in this case.



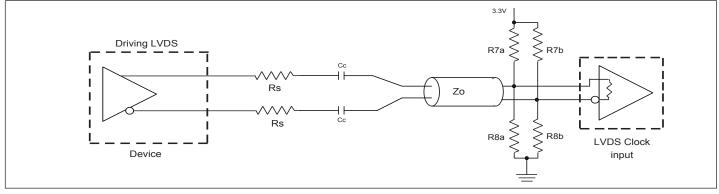


#### **Test Loads**





#### **Alternate Terminations**



### **Driving LVDS inputs with the PI6CFGL201B**

	Value	
Component	Receiver has termination	Receiver does not have termination
R7a, R7b	10Κ Ω	140 Ω
R8a, R8b	5.6Κ Ω	75 Ω
Cc	0.1 uF	0.1 uF
Vcm	1.2 volts	1.2 volts







# Serial Data Interface (SMBus)

This part is a slave only device that supports blocks read and block write protocol using a single 7-bit address and read/write bit as shown below.

Read and write block transfers can be stopped after any complete byte transfer by issuing STOP.

#### **Address Assignment**

Refer to SMBus Address Selection Table.

#### **Data Protocol**

(Write)

1 bit	8 bits	1	8 bits	1	8 bits	1	8 bits	1	8 bits	1	1 bit
Start bit	Slave Addr: D4	Ack	Register offset	Ack	Byte Count=N	Ack	Data Byte 0	Ack	Data Byte N-1	Ack	Stop bit

(Read)

1 bit	8 bits	1	8 bits	1	1	8 bits	1	8 bits	1	8 bits	1	8 bits	1	1 bit
Start bit	Slave Addr: D4		Register offset	Ack	Repeat	Slave Addr: D5	Ack	Byte Count=N	Ack	Data Byte 0	Ack	 Data Byte N-1	NOT Ack	Stop bit

Note:

1. Register offset for indicating the starting register for indexed block write and indexed block read. Byte Count in write mode cannot be 0.





## **SMBus Table: Output Enable Register**

BYT	E 0					
Bit	Name	Control Function	Туре	0	1	Default
7	Reserved					1
6	Reserved					1
5	Reserved					1
4	Reserved					1
3	Reserved					1
2	OE1	Output Enable	RW	Low/Low	Enabled	1
1	OE0	Output Enable	RW	Low/Low	Enabled	1
0	Reserved					1

### SMBus Table: SS Readback and Vhigh Control Register

BYT	TE 1						
Bit	Name	Control Function	Туре	0	1	Default	
7	SSENRB1	SS Enable Readback Bit1	R	00' for SS_EN_tri = 0,	or SS_EN_tri = 0, '01' for SS_EN_tri = 'M',		
6	SSENRB0	SS Enable Readback Bit0	R	'11 for SS_EN_tri = '1'	for SS_EN_tri = '1'		
5	SSEN_SWCNTRL	Enable SW control of SS	RW	SS control locked Values in B1[4:3] control SS amount.		0	
4	SSENSW1	SS Enable Software Ctl Bit1	RW <sup>1</sup>	00' = SS Off, '01' = -0.2	5% SS,	0	
3	SSENSW0	SS Enable Software Ctl Bit0	RW <sup>1</sup>	'10' = Reserved, '11'= -0	0.5% SS	0	
2	Reserved					1	
1	AMPLITUDE 1	Controle Octoort Amerility de	RW	00 = 0.6 V	01 = 0.7 V	1	
0	AMPLITUDE 0	Controls Output Amplitude	RW	10= 0.8V	11 = 0.9 V	0	

# SMBus Table: CLK Slew Rate Control Register

BYTE 2									
Bit	Name	Control Function	Туре	0	1	Default			
7	Reserved					1			
6	Reserved					1			
5	Reserved					1			
4	Reserved					1			
3	Reserved					1			
2	SLEWRATESEL CLK1	Adjust Slew Rate of CLK1	RW	1.5V/ns	3.0V/ns	1			
1	SLEWRATESEL CLK0	Adjust Slew Rate of CLK0	RW	1.5V/ns	3.0V/ns	1			
0	Reserved					1			





# SMBus Table: REF1.8 Control Register

BYT	E 3					
Bit	Name	<b>Control Function</b>	Туре	0	1	Default
7	DEELO	Classe Dista Countrial	RW	00 = 0.9V/ns	01 =1.3V/ns	0
6	REF1.8	Slew Rate Control	RW	10 = 1.6V/ns	11 = 1.8V/ns	1
5	REF1.8 Power Down Function	Wake-ON-LAN Enable for REF1.8	RW	REF1.8 does not run in Power Down	REF1.8 runs in Power Down	0
4	REF1.8 OE	REF1.8 Output Enable	RW	Low	Enabled	1
3	Reserved					1
2	Reserved					1
1	Reserved					1
0	Reserved					1

# Byte 4 is reserved and reads back 'hFF'.

#### **SMBus Table: Revision and Vendor ID Register**

BYT	TE 5						
Bit	Name	<b>Control Function</b>	Туре	0	0 1		
7	RID3		R			0	
6	RID2		R				
5	RID1	Revision ID	R	A rev = $000$	A rev = $0000$		
4	RID0		R			0	
3	VID3		R			0	
2	VID2		R			0	
1	VID1	VENDOR ID	R			0	
0	VID0		R			0	





# SMBus Table: Device Type/Device ID

BYI	<b>FE 6</b>						
Bit	Name	<b>Control Function</b>	Туре	0	1	Default	
7	Device Type1	Deries Terre	R	00 = FGV, 01	00 = FGV, 01 = DBV,		
6	Device Type0	Device Type	R	10 = DMV, 11= Reserved		0	
5	Device ID5		R				
4	Device ID4		R			0	
3	Device ID3		R			0	
2	Device ID2	Device ID	R	-00010 binary	00010 binary or 02 hex		
1	Device ID1		R			1	
0	Device ID0		R		0		

### **SMBus Table: Byte Count Register**

ВҮТ	BYTE 7									
Bit	Name	<b>Control Function</b>	Туре	0	1	Default				
7	Reserved					0				
6	Reserved					0				
5	Reserved					0				
4	Reserved					0				
3	Reserved					0				
2	Reserved					0				
1	Reserved					0				
0	Reserved					0				



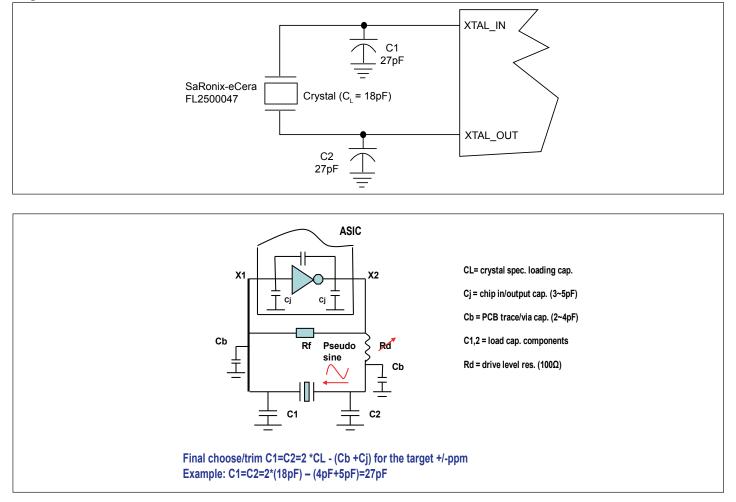


# **Application Notes**

### **Crystal circuit connection**

The following diagram shows crystal circuit connection with a parallel crystal. For the CL=18pF crystal, it is suggested to use C1= 27pF, C2= 27pF. C1 and C2 can be adjusted to fine tune to the target ppm of crystal oscillator according to different board layouts.

### **Crystal Oscillator Circuit**



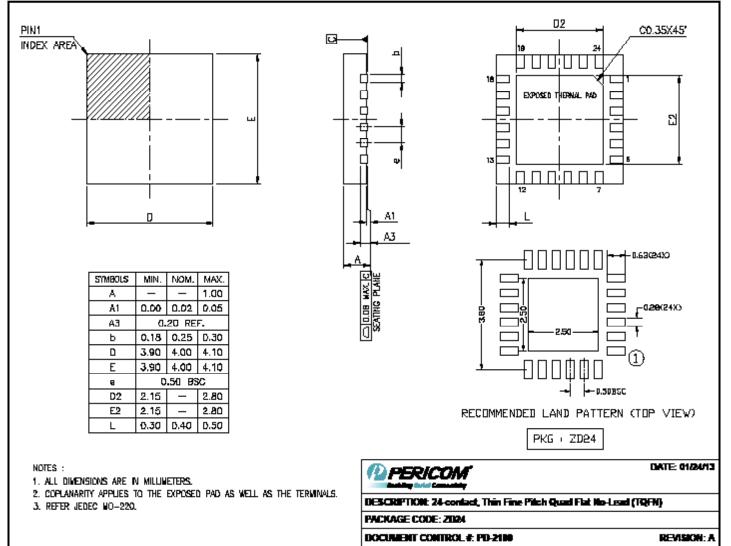
#### **Thermal Characteristics**

Symbol	Parameters	Min.	Туре	Max.	Units
θJA	Thermal Resistance Junction to Ambient		54.4		°C/W
θЈС	Thermal Resistance Junction to Case		40.8		°C/W





#### Packaaina Mechanical: 24-Pin TQFN (ZD)



13-0017

#### Ordering Information<sup>(1-3)</sup>

Ordering Number	Package Code	Package Description	Operating Temperature
PI6CFGL201BZDIE	ZD	24-pin, Thin Fine Pitch Quad Flat No-Lead (TQFN)	Industrial
PI6CFGL201BZDIEX	ZD	24-pin, Thin Fine Pitch Quad Flat No-Lead (TQFN), Tape & Reel	Industrial

#### Notes:

1. 1Thermal characteristics can be found on the company web site at www.pericom.com/packaging/

2. E = Pb-free and Green

3. Adding an X suffix = Tape/Reel

Rev C

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单击下面可查看定价,库存,交付和生命周期等信息

>>Diodes Incorporated(达迩科技(美台))